

# NPN SILICON RF TRANSISTOR

**DESCRIPTION:**

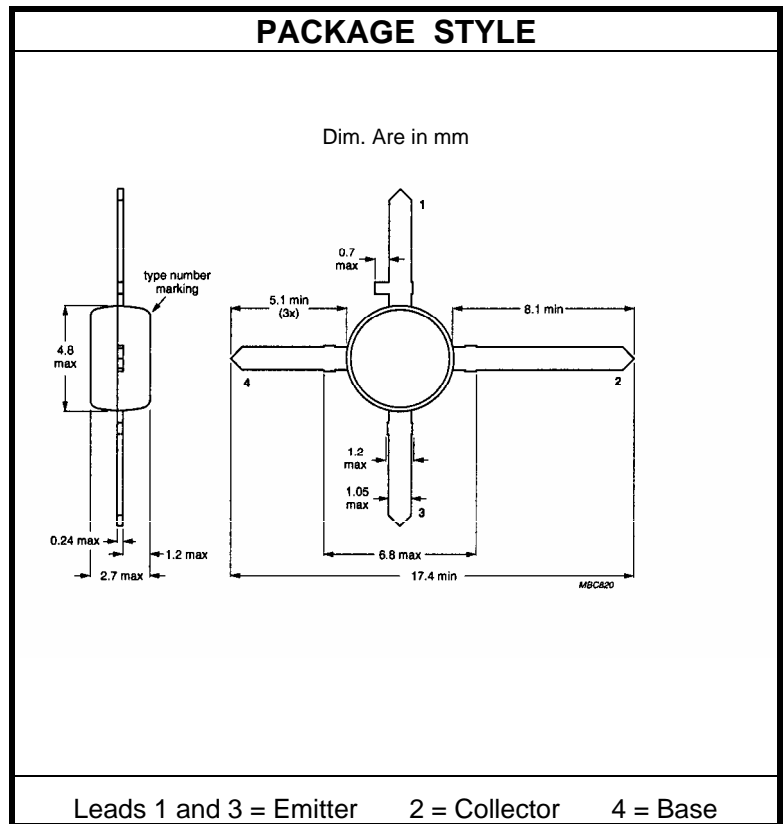
The **ASI MRF901** is Designed for high gain. Low noise small-signal amplifiers. Applications up to 2.5 GHz.

**FEATURES:**

- Low Noise Figure
- High Gain
- **Common Emitter**

**MAXIMUM RATINGS**

$I_C$	30 mA
$V_{CBO}$	25 V
$V_{CEO}$	15 V
$V_{EBO}$	2.0 V
$P_{DISS}$	0.375 W @ $T_C = 75\text{ }^\circ\text{C}$
$T_J$	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$T_{STG}$	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$\theta_{JC}$	200 $^\circ\text{C/W}$


**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 0.1\text{ mA}$			25			V
$BV_{CEO}$	$I_C = 1.0\text{ mA}$			15			V
$BV_{EBO}$	$I_E = 0.1\text{ mA}$			2.0			V
$I_{CBO}$	$V_{CB} = 15\text{ V}$					50	nA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$	$I_C = 5.0\text{ mA}$		30	80	200	---
$C_{cb}$	$V_{CB} = 10\text{ V}$	$f = 1.0\text{ MHz}$			0.40	1.0	pF
$f_T$	$V_{CE} = 10\text{ V}$	$I_C = 15\text{ mA}$	$f = 1.0\text{ GHz}$		4.5		GHz
$NF_{MIN}$	$V_{CE} = 6.0\text{ V}$	$I_C = 15\text{ mA}$	$f = 1.0\text{ GHz}$		2.0	2.5	dB